

PSMN2R2-30YLC

N-channel 30 V 2.15m Ω logic level MOSFET in LFPAK using NextPower technology

Rev. 02 — 3 May 2011

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, and QOSS for high system efficiencies at low and high loads

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

- Power OR-ing
- Server power supplies
- Sync rectifier

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	30	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2		-	-	141	W
T _j	junction temperature			-55	-	175	°C
Static cha	aracteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{}$		-	2.3	2.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_i = 25 \text{ °C}; \text{ see Figure 12}$		-	1.8	2.15	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic	characteristics					
Q_{GD}	gate-drain charge	V_{GS} = 4.5 V; I_D = 25 A; V_{DS} = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	8	-	nC
Q _{G(tot)}	total gate charge	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 15 \text{ V}; \text{see } \underline{\text{Figure 14}};$ $\text{see } \underline{\text{Figure 15}}$	-	26	-	nC

^[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

I doic L.		, information					
Pin	Symbol	Description	Simplified outline	Graphic symbol			
1	S	source		_			
2	S	source	mb (D			
3	S	source					
4	G	gate	9				
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S			
			SOT669 (LFPAK; Power-SO8)				

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN2R2-30YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PSMN2R2-30YLC	2C230L

^{[1] % =} placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		<u> </u>				
Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	30	V
V_{DGR}	drain-gate voltage	25 °C \leq T _j \leq 175 °C; R _{GS} = 20 k Ω		-	30	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	[1]	-	100	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	<u>[1]</u>	-	100	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 4		-	765	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	141	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
V _{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)		630	-	V
Source-drain of	diode					
Is	source current	T _{mb} = 25 °C	[1]	-	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	765	Α
Avalanche rug	gedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le$ 30 V; R_{GS} = 50 Ω ; unclamped; see Figure 3		-	92	mJ

[1] Continuous current is limited by package.

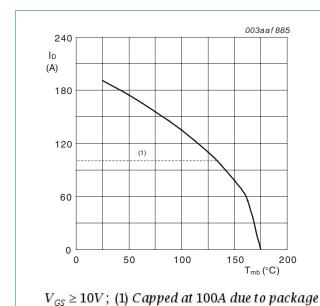


Fig 1. Continuous drain current as a function of mounting base temperature

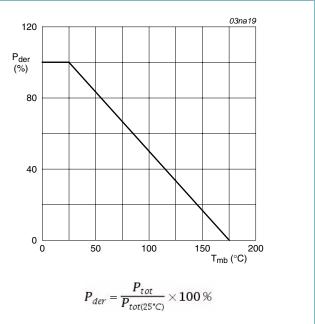


Fig 2. Normalized total power dissipation as a function of mounting base temperature

PSMN2R2-30YLC

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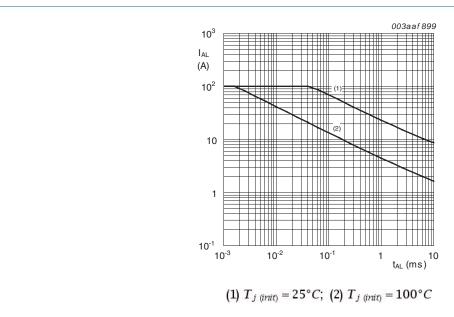
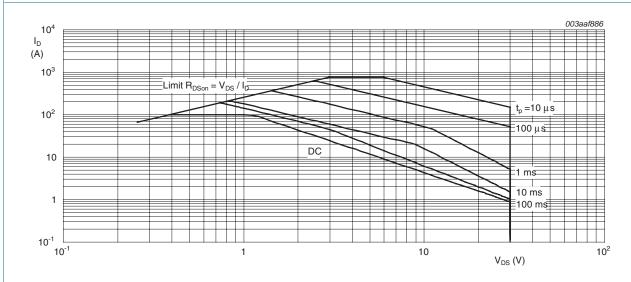


Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time



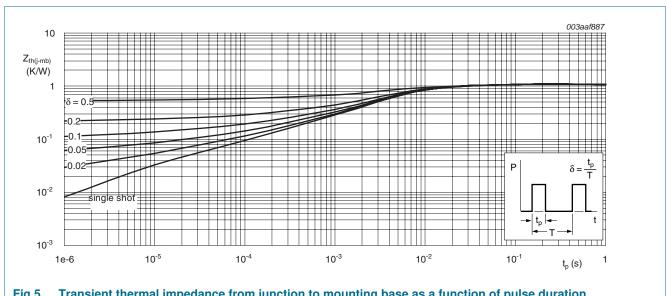
 $T_{mb} = 25$ °C; I_{DM} is a single pulse

Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

Thermal characteristics

Table 6. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	0.92	1.06	K/W



Transient thermal impedance from junction to mounting base as a function of pulse duration

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	٧
	voltage	$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{V}; T_j = -55 ^{\circ}\text{C}$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see Figure 10; see Figure 11	1.05	1.49	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.25	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 12	-	2.3	2.8	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 150 ^{\circ}\text{C};$ see Figure 12; see Figure 13	-	-	4.6	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	1.8	2.15	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 150 °C;$ see Figure 12; see Figure 13	-	-	3.55	mΩ
R _G	gate resistance	f = 1 MHz	-	8.0	1.6	Ω
Dynamic cl	haracteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 10 \text{ V}$; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	55	-	nC
		$I_D = 25 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 4.5 \text{ V}$; see Figure 14; see Figure 15	-	26	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	21	-	nC
Q_{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	7.3	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	5.2	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	2.1	-	nC
Q_{GD}	gate-drain charge		-	8	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25 \text{ A}$; $V_{DS} = 15 \text{ V}$; see Figure 14; see Figure 15	-	2.43	-	V
C _{iss}	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	3310	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	651	-	pF
C _{rss}	reverse transfer capacitance		-	239	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 0.6 \Omega; V_{GS} = 4.5 \text{ V};$	-	26	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	36	-	ns
t _{d(off)}	turn-off delay time		-	47	-	ns
t _f	fall time		-	23	-	ns

Table 7. **Characteristics** ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q_{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; f = 1 \text{ MHz}; $ $T_j = 25 \text{ °C}$	-	18.4	-	nC
Source-drain	n diode					
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 17	-	0.8	1.1	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	37	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	-	37	-	nC
t _a	reverse recovery rise time	$V_{GS} = 0 \text{ V}; I_S = 25 \text{ A};$	-	21	-	ns
t _b	reverse recovery fall time	$dI_S/dt = -100 A/\mu s$; $V_{DS} = 15 V$; see Figure 18	-	16	-	ns

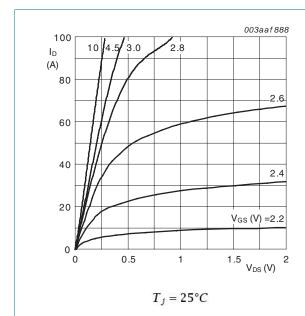


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values

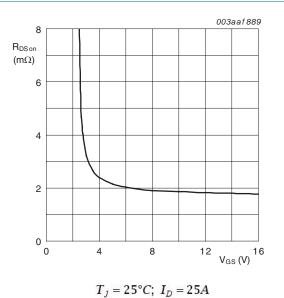


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

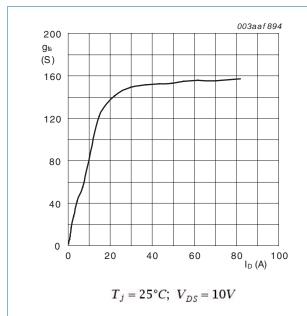


Fig 8. Forward transconductance as a function of drain current; typical values

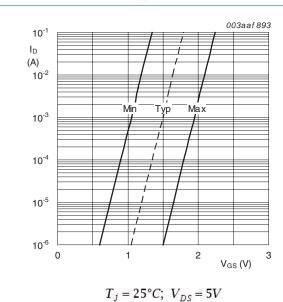


Fig 10. Sub-threshold drain current as a function of gate-source voltage

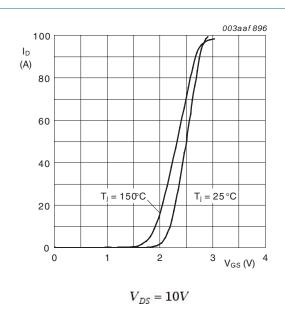


Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

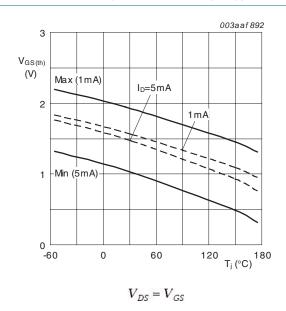


Fig 11. Gate-source threshold voltage as a function of junction temperature

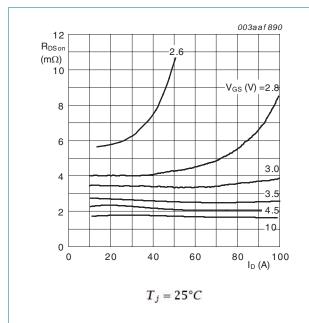


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

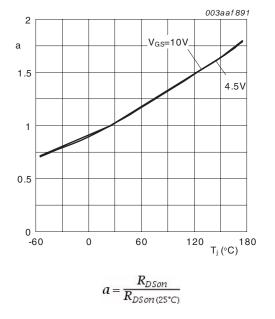


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

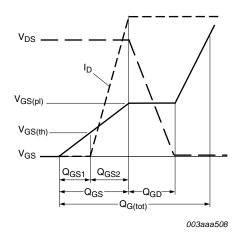
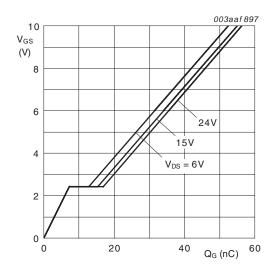
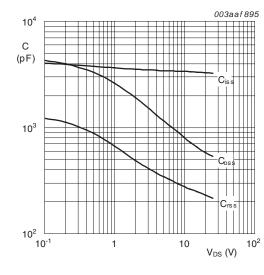


Fig 14. Gate charge waveform definitions



 $T_j = 25^{\circ}C; \ I_D = 25A$

Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

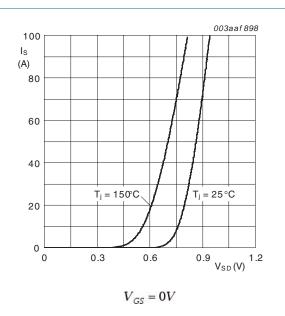


Fig 17. Source current as a function of source-drain voltage; typical values

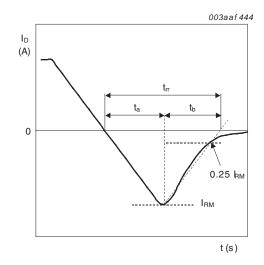
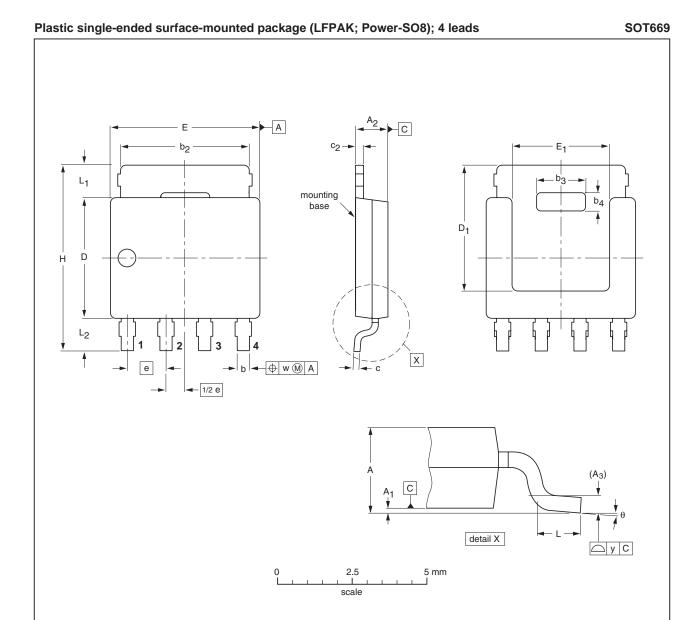


Fig 18. Reverse recovery timing definition

8. Package outline



DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁	A ₂	A ₃	b	b ₂	b ₃	b ₄	С	c ₂	D ⁽¹⁾	D ₁ ⁽¹⁾ max	E ⁽¹⁾	E ₁ ⁽¹⁾	е	Н	L	L ₁	L ₂	w	у	θ
mm	1.20 1.01	0.15 0.00	1.10 0.95	0.25	0.50 0.35	4.41 3.62	2.2 2.0	0.9 0.7	0.25 0.19	0.30 0.24	4.10 3.80	4.20	5.0 4.8	3.3 3.1	1.27	6.2 5.8	0.85 0.40	1.3 0.8	1.3 0.8	0.25	0.1	8° 0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE	NE REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT669		MO-235				06-03-16 11-03-25

Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

PSMN2R2-30YLC

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9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes					
PSMN2R2-30YLC v.2	20110503	Product data sheet	-	PSMN2R2-30YLC v.1					
Modifications:	Status changed from preliminary to product.Various changes to content.								
PSMN2R2-30YLC v.1	20110317	Preliminary data sheet	-	-					

10. Legal information

10.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

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PSMN2R2-30YLC

N-channel 30 V 2.15mΩ logic level MOSFET in LFPAK using NextPower

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12. Contents

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